

AMENDMENTS TO THE CLAIMS

1. **(Currently amended)** A positive resist composition comprising: a resin component (A) which comprises ~~A resin for a positive resist composition, comprising:~~
 a structural unit (a1) represented by a general formula (I) shown below:



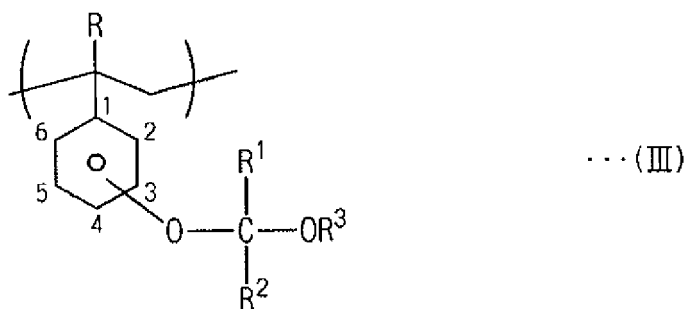
(wherein, R represents -H or -CH₃),

a structural unit (a2) represented by a general formula (II) shown below:



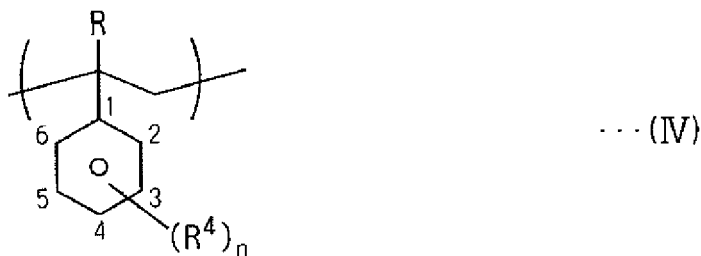
(wherein, R represents -H or -CH₃, and X represents an acid dissociable, dissolution inhibiting group, which is an alkyl group with a tertiary carbon atom in which said tertiary carbon atom is bonded to an ester group),

a structural unit (a3) represented by a general formula (III) shown below:



(wherein, R and R¹ each represent, independently, -H or -CH₃, R² represents -CH₃ or -C₂H₅, and R³ represents a lower alkyl group), and

a structural unit (a4) represented by a general formula (IV) shown below:

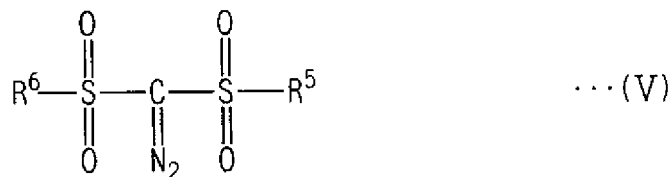


(wherein, R represents -H or -CH₃, R⁴ represents a lower alkyl group, and n represents either 0, or an integer from 1 to 3), and an acid generator (B) that generates acid upon exposure, wherein said component (B) comprises a diazomethane-based acid generator (B1) and an onium salt-based acid generator (B2), wherein the weight ratio of B1 to B2 is within a range from 1:1 to 10:1.

2. **(Canceled)**

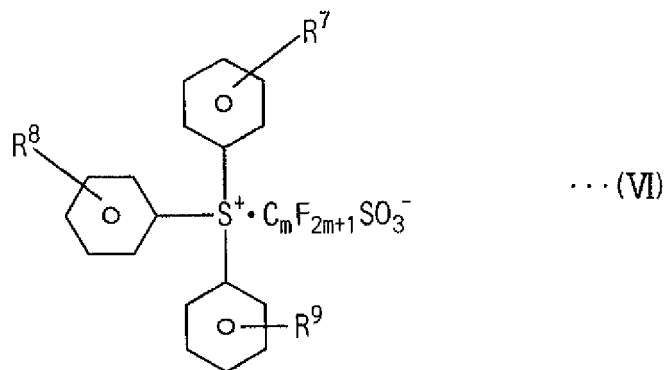
3. **(Canceled)**

4. **(Currently amended)** A positive resist composition according to claim [[3]] 1, wherein said component (B1) comprises a compound represented by a general formula (V) shown below:



(wherein, R⁵ and R⁶ each represent, independently, a straight-chain, branched, or cyclic alkyl group of 3 to 7 carbon atoms).

5. **(Original)** A positive resist composition according to claim 4, wherein said component (B2) comprises a compound represented by a general formula (VI) shown below:



(wherein, R^7 , R^8 and R^9 each represent, independently, a hydrogen atom, or an alkyl group or alkoxy group of 1 to 4 carbon atoms, and m represents an integer from 1 to 10).

6. **(Currently amended)** A positive resist composition according to claim [[2]] 1, further comprising a nitrogen-containing organic compound (D).

7. **(Currently amended)** A laminate, comprising a resist layer formed from a positive resist composition according to claim [[2]] 1 provided on top of a substrate.

8. **(Currently amended)** A method for forming a resist pattern, comprising the steps of: (1) providing a resist layer formed from a positive resist composition according to claim [[2]] 1 on top of a substrate, (2) conducting selective exposure of said resist layer, (3) performing post exposure baking of said selectively exposed resist layer, and (4) conducting alkali developing of said post exposure baked resist layer.

9. **(Currently amended)** A positive resist composition, which is a chemically amplified positive resist composition for forming a resist layer, either on top of a substrate and a magnetic film provided on top of said substrate, or on top of a metallic oxidation prevention film provided on top of said magnetic film, wherein said composition comprises:

a resin component (A'), which exhibits increased alkali solubility under action of acid, and comprises a structural unit (a1) represented by a general formula (I) shown below:



(wherein, R represents -H or -CH₃), and

a structural unit (a2) represented by a general formula (II) shown below:



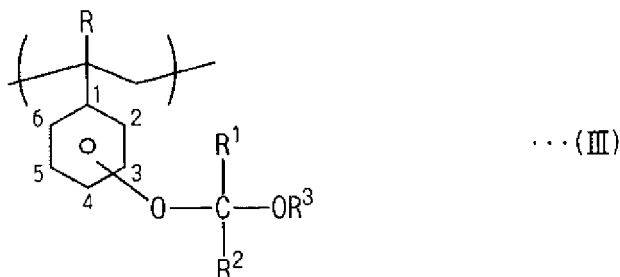
(wherein, R represents -H or -CH₃, and X represents an acid dissociable, dissolution inhibiting group, which is an alkyl group with a tertiary carbon atom in which said tertiary carbon atom is bonded to an ester group),

a diazomethane-based acid generator (B1), and

an onium salt-based acid generator (B2),

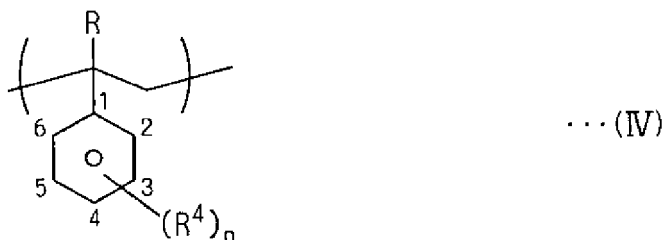
wherein the weight ratio of B1 to B2 is within a range of 1:1 to 1:10.

10. **(Original)** A positive resist composition according to claim 9, wherein said component (A') further comprises a structural unit (a3) represented by a general formula (III) shown below:



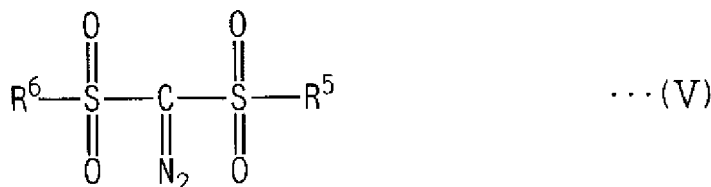
(wherein, R and R¹ each represent, independently, -H or -CH₃, R² represents -CH₃ or -C₂H₅, and R³ represents a lower alkyl group).

11. **(Original)** A positive resist composition according to claim 9, wherein said component (A') further comprises a structural unit (a4) represented by a general formula (IV) shown below:



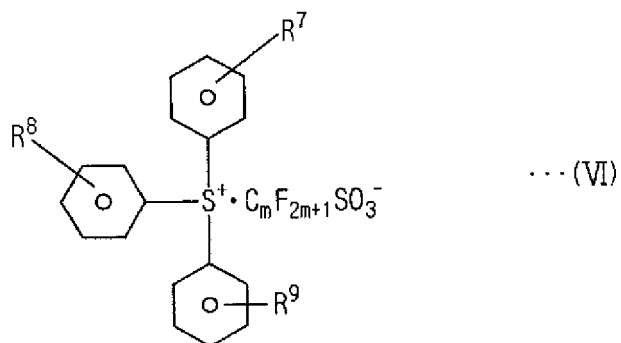
(wherein, R represents -H or -CH₃, R⁴ represents a lower alkyl group, and n represents either 0, or an integer from 1 to 3).

12. **(Original)** A positive resist composition according to claim 9, wherein said component (B1) comprises a compound represented by a general formula (V) shown below:



(wherein, R⁵ and R⁶ each represent, independently, a straight-chain, branched, or cyclic alkyl group of 3 to 7 carbon atoms).

13. **(Original)** A positive resist composition according to claim 9, wherein said component (B2) comprises a compound represented by a general formula (VI) shown below:



(wherein, R^7 , R^8 and R^9 each represent, independently, a hydrogen atom, or an alkyl group or alkoxy group of 1 to 4 carbon atoms, and m represents an integer from 1 to 10).

14. **(Original)** A positive resist composition according to claim 9, further comprising a nitrogen-containing organic compound (D).

15. **(Original)** A positive resist composition according to claim 9, wherein a principal component of said magnetic film comprises one or more metals selected from a group consisting of iron, cobalt, and nickel.

16. **(Original)** A positive resist composition according to claim 9, wherein a principal component of said oxidation prevention film comprises one or more materials selected from a group consisting of tantalum and aluminum oxide (Al_2O_3).

17. **(Currently amended)** A laminate, comprising a substrate, either a magnetic film provided on top of said substrate, or said magnetic film and a metallic oxidation prevention film provided thereon, and a resist layer formed from a positive resist composition ~~according to claim 9~~ provided on top of either said magnetic film or said magnetic film and said metallic oxidation prevention film provided thereon, wherein said positive resist composition comprises: a resin component (A'), which exhibits increased alkali solubility under action of acid, and comprises a structural unit (a1) represented by a general formula (I) shown below:



(wherein, R represents -H or -CH₃), and

a structural unit (a2) represented by a general formula (II) shown below:



(wherein, R represents -H or -CH₃, and X represents an acid dissociable, dissolution inhibiting group, which is an alkyl group with a tertiary carbon atom in which said tertiary carbon atom is bonded to an ester group),

a diazomethane-based acid generator (B1), and

an onium salt-based acid generator (B2).

18. **(Original)** A laminate according to claim 17, wherein a principal component of said magnetic film comprises one or more metals selected from a group consisting of iron, cobalt, and nickel.

19. **(Original)** A laminate according to claim 17, wherein a principal component of said oxidation prevention film comprises one or more materials selected from a group consisting of tantalum and aluminum oxide (Al₂O₃).

20. **(Currently amended)** A method for forming a resist pattern, comprising the steps of: (1) providing a resist layer formed from a positive resist composition according to claim 9, either on top of a substrate and a magnetic film provided on top of said substrate, or on top of a metallic oxidation prevention film provided on top of said magnetic film, (2) conducting selective exposure of said resist layer, (3) performing post exposure baking of said selectively exposed resist layer, and (4) conducting alkali developing of said post exposure baked resist layer, wherein said positive resist composition comprises:

a resin component (A'), which exhibits increased alkali solubility under action of acid, and comprises a structural unit (a1) represented by a general formula (I) shown below:



(wherein, R represents -H or -CH₃), and

a structural unit (a2) represented by a general formula (II) shown below:



(wherein, R represents -H or -CH₃, and X represents an acid dissociable, dissolution inhibiting group, which is an alkyl group with a tertiary carbon atom in which said tertiary carbon atom is bonded to an ester group),

a diazomethane-based acid generator (B1), and

an onium salt-based acid generator (B2).

21. **(Original)** A method for forming a resist pattern according to claim 20, wherein a material in which a principal component comprises one or more metals selected from a group consisting of iron, cobalt, and nickel is used as said magnetic film.

22. **(Original)** A positive resist composition according to claim 20, wherein a material in which a principal component comprises one or more materials selected from a group consisting of tantalum and aluminum oxide (Al₂O₃) is used as said oxidation prevention film.